John T Leonard

List of Publications by Year
in descending order

16	571	840776 11	1058476 14
papers	citations	h-index	g-index

17	17	17	352
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Demonstration of GaN-based vertical-cavity surface-emitting lasers with buried tunnel junction contacts. Optics Express, 2019, 27, 31621.	3.4	33
2	Continuous-wave operation of m-plane GaN-based vertical-cavity surface-emitting lasers with a tunnel junction intracavity contact. Applied Physics Letters, 2018, 112, .	3.3	44
3	GaN-based vertical-cavity surface-emitting lasers with tunnel junction contacts grown by metal-organic chemical vapor deposition. Applied Physics Express, 2018, 11, 062703.	2.4	51
4	Continuous-wave operation of nonpolar GaN-based vertical-cavity surface-emitting lasers. , 2018, , .		4
5	Smooth and selective photo-electrochemical etching of heavily doped GaN:Si using a mode-locked 355 nm microchip laser. Applied Physics Express, 2017, 10, 011001.	2.4	13
6	Nonpolar III-nitride vertical-cavity surface-emitting laser with a photoelectrochemically etched air-gap aperture. Applied Physics Letters, 2016, 108, 031111.	3.3	39
7	Demonstration of a III-nitride edge-emitting laser diode utilizing a GaN tunnel junction contact. Optics Express, 2016, 24, 7816.	3.4	58
8	Flip-chip blue LEDs grown on bulk GaN substrates utilizing photoelectrochemical etching for substrate removal. Applied Physics Express, 2016, 9, 056502.	2.4	10
9	Comparison of nonpolar III-nitride vertical-cavity surface-emitting lasers with tunnel junction and ITO intracavity contacts. Proceedings of SPIE, 2016, , .	0.8	8
10	GHz modulation bandwidth from single-longitudinal mode violet-blue VCSEL using nonpolar InGaN/GaN QWs. , 2016, , .		7
11	Smooth e-beam-deposited tin-doped indium oxide for III-nitride vertical-cavity surface-emitting laser intracavity contacts. Journal of Applied Physics, 2015, 118, .	2.5	24
12	Selective and controllable lateral photoelectrochemical etching of nonpolar and semipolar InGaN/GaN multiple quantum well active regions. Applied Physics Express, 2015, 8, 066502.	2.4	7
13	Demonstration of low resistance ohmic contacts to p-type (202Ì„1Ì„) GaN. Semiconductor Science and Technology, 2015, 30, 075007.	2.0	12
14	Nonpolar III-nitride vertical-cavity surface-emitting lasers incorporating an ion implanted aperture. Applied Physics Letters, 2015, 107, .	3.3	85
15	Demonstration of a III-nitride vertical-cavity surface-emitting laser with a III-nitride tunnel junction intracavity contact. Applied Physics Letters, 2015, 107, .	3.3	122
16	Nonpolar III-nitride vertical-cavity surface emitting lasers with a polarization ratio of 100% fabricated using photoelectrochemical etching. Applied Physics Letters, 2014, 105, .	3.3	54